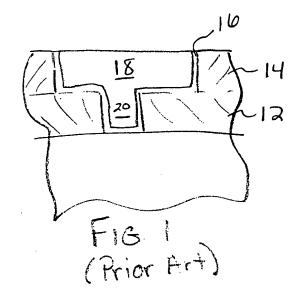
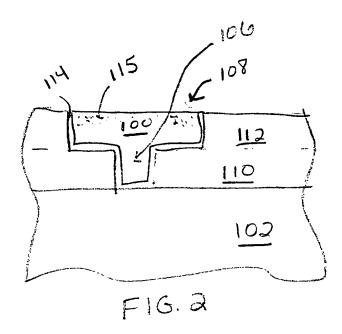
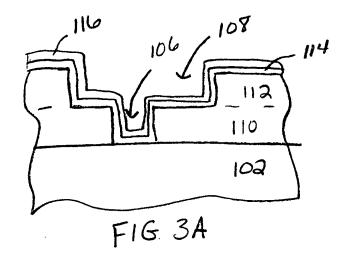
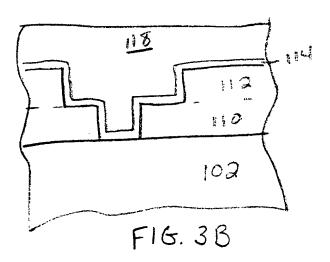
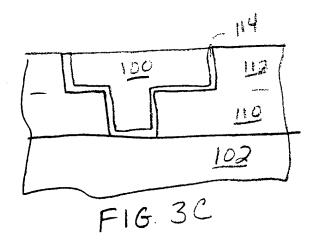
1 of 6 J. Garner

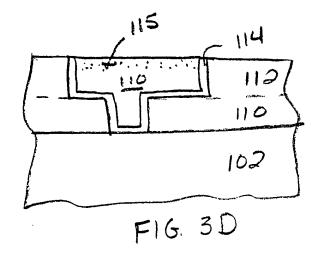


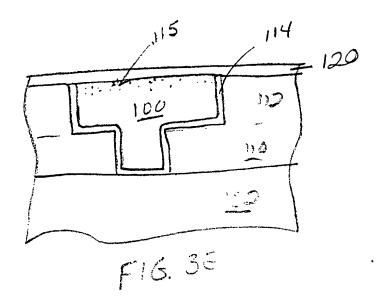




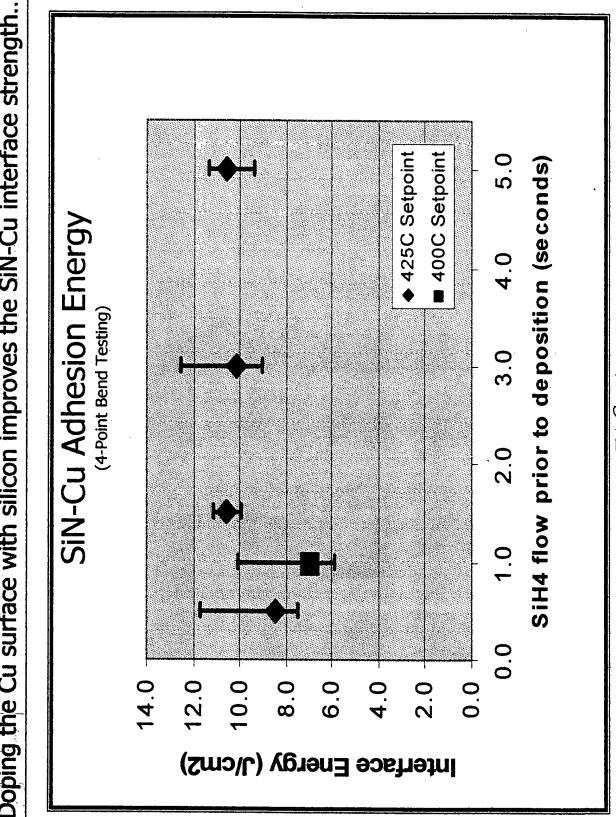




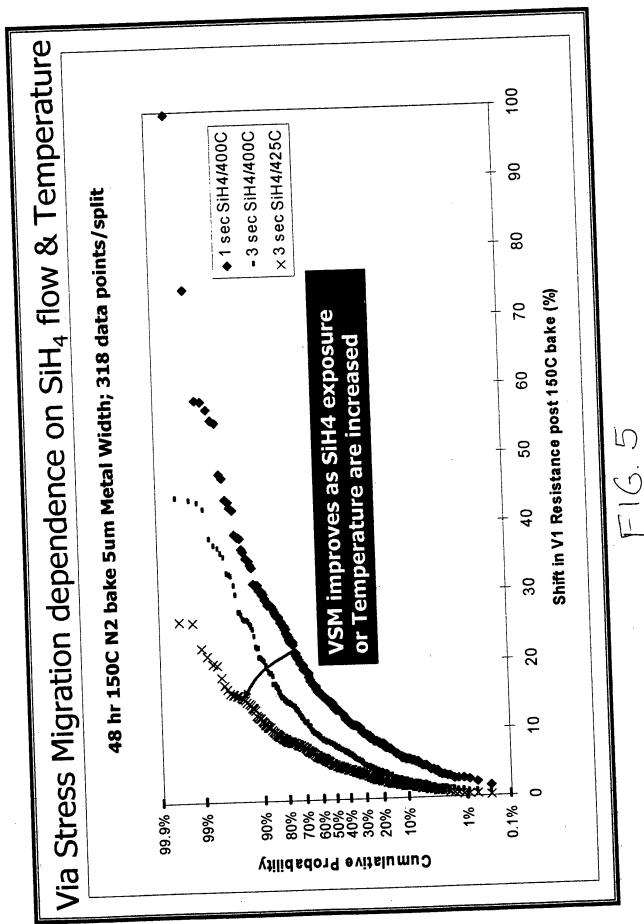




Doping the Cu surface with silicon improves the SiN-Cu interface strength...

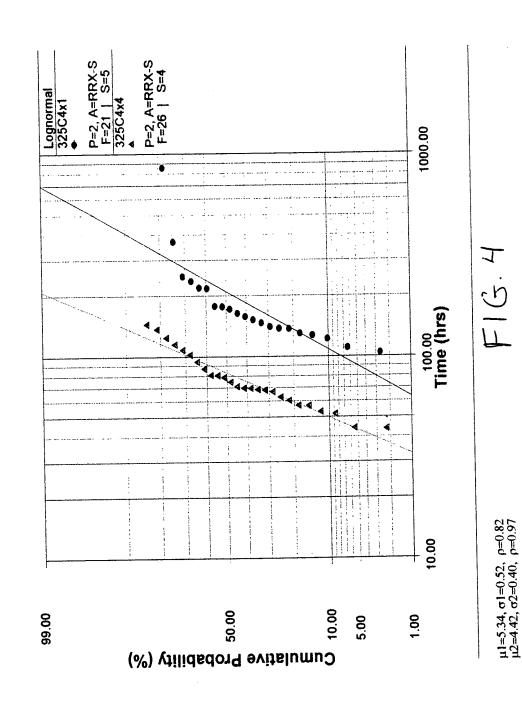


F16.6



9 fos 85398 -11

EM:@325C, 1.5MA/cm2



9 + 0 h. 3 & Z9 & - 1 <u>L</u>